

Silicon Epitaxial Planar Switching Diode

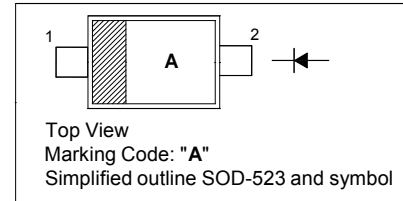
for ultra high speed switching application

Features

- Fast reverse recovery time
- Small total capacitance
- Low forward voltage

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

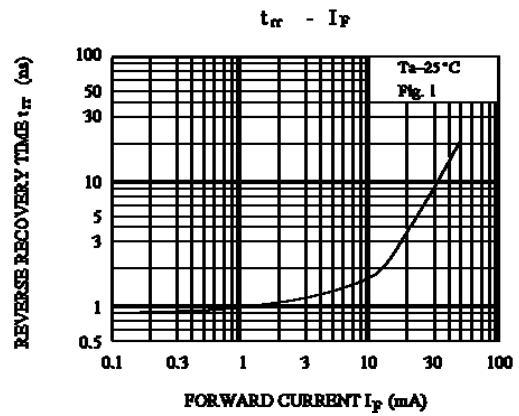
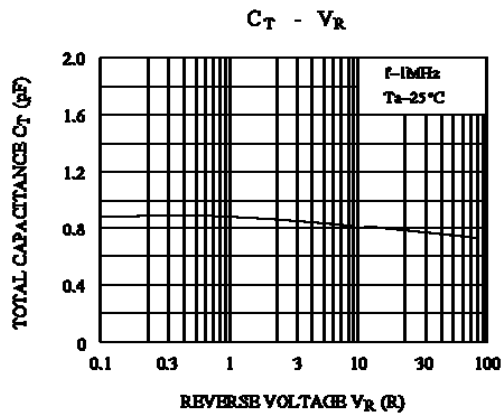
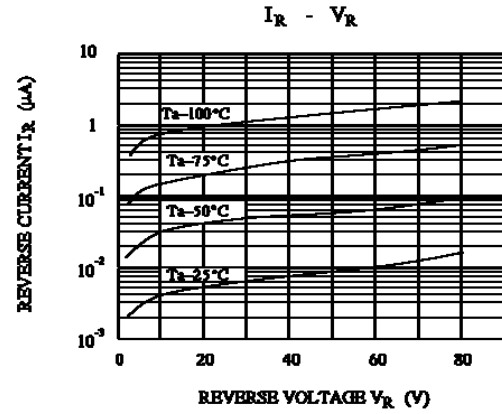
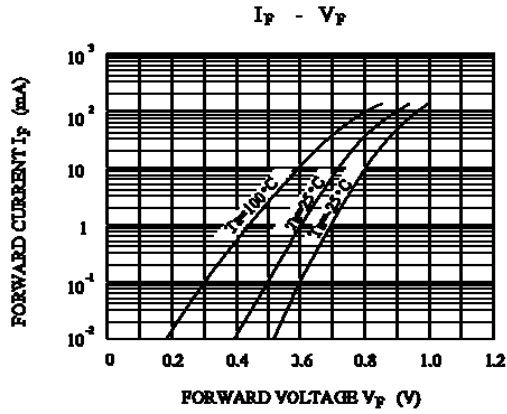


Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Peak Forward Current	I _{FM}	300	mA
Surge Forward Current (10 ms)	I _{FSM}	2	A
Power Dissipation	P _D	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at V _R = 80 V	I _R	0.5	μA
Total Capacitance at V _R = 0 V, f = 1 MHz	C _T	3	pF
Reverse Recovery Time at I _{rr} = 0.1 X I _R , I _F = I _R = 10 mA, R _L = 100 Ω	t _{rr}	4	ns





CHINA BASE
INTERNATIONAL

SOD-523

SDS160EWT

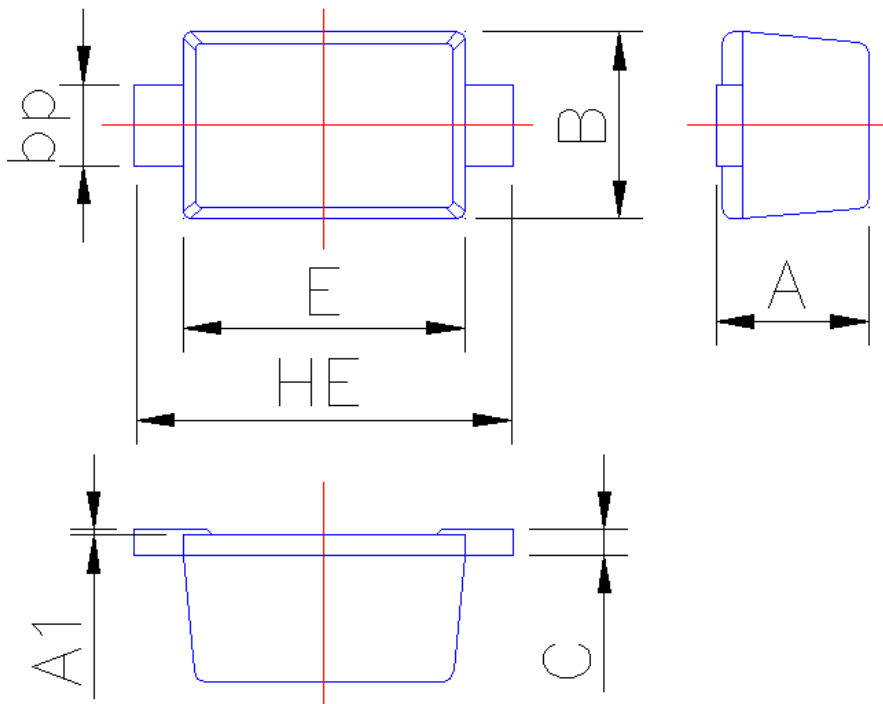


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70